

# IS61C1024 IS61C1024L



## 128K x 8 HIGH-SPEED CMOS STATIC RAM

JULY 1997

### FEATURES

- High-speed access time: 12, 15, 20, 25 ns
- Low active power: 600 mW (typical)
- Low standby power: 500  $\mu$ W (typical) CMOS standby
- Output Enable ( $\overline{OE}$ ) and two Chip Enable ( $\overline{CE1}$  and CE2) inputs for ease in applications
- Fully static operation: no clock or refresh required
- TTL compatible inputs and outputs
- Single 5V ( $\pm 10\%$ ) power supply
- Low power version available: IS61C1024L
- Commercial and industrial temperature ranges available

### DESCRIPTION

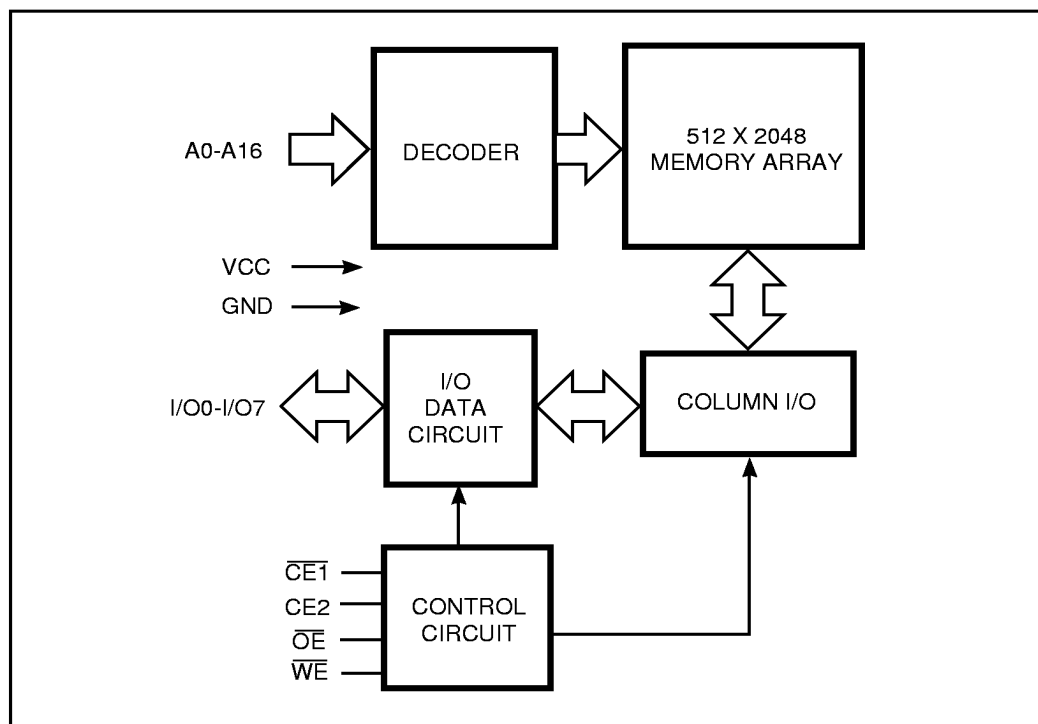
The *ISSI* IS61C1024 and IS61C1024L are very high-speed, low power, 131,072-word by 8-bit CMOS static RAMs. They are fabricated using *ISSI's* high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields higher performance and low power consumption devices.

When  $\overline{CE1}$  is HIGH or CE2 is LOW (deselected), the device assumes a standby mode at which the power dissipation can be reduced by using CMOS input levels.

Easy memory expansion is provided by using two Chip Enable inputs,  $\overline{CE1}$  and CE2. The active LOW Write Enable ( $\overline{WE}$ ) controls both writing and reading of the memory.

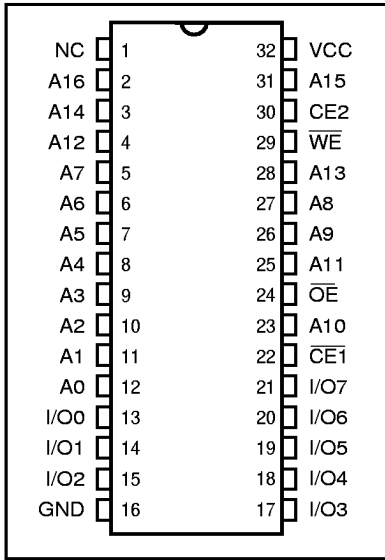
The IS61C1024 and IS61C1024L are available in 32-pin 300-mil and 400-mil plastic DIP and SOJ, and TSOP (type 1) packages.

### FUNCTIONAL BLOCK DIAGRAM

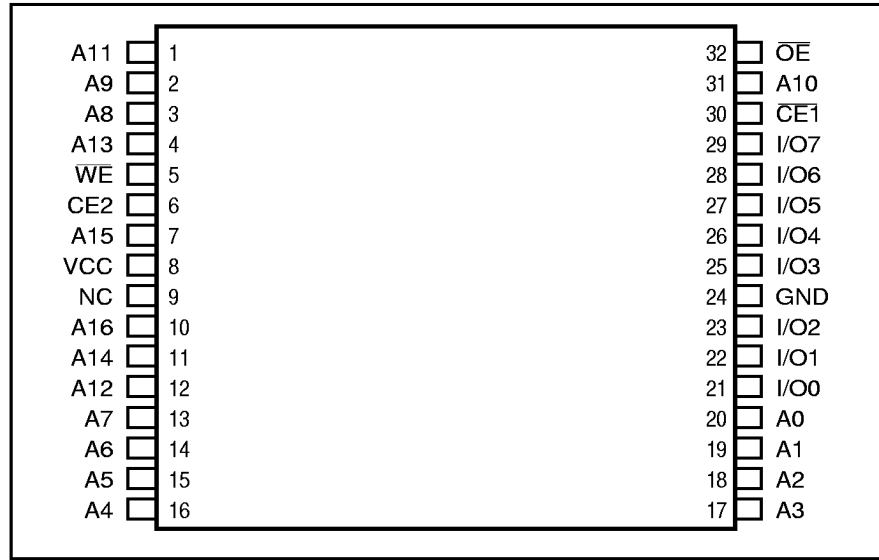


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**PIN CONFIGURATION**  
32-Pin SOJ



**PIN CONFIGURATION**  
32-Pin TSOP (Type 1)



**PIN DESCRIPTIONS**

A0-A16	Address Inputs
$\overline{CE1}$	Chip Enable 1 Input
CE2	Chip Enable 2 Input
$\overline{OE}$	Output Enable Input
$\overline{WE}$	Write Enable Input
I/O0-I/O7	Input/Output
Vcc	Power
GND	Ground

**OPERATING RANGE**

Range	Ambient Temperature	Vcc <sup>(1)</sup>
Commercial	0°C to +70°C	5V ± 10%
Industrial	-40°C to +85°C	5V ± 10%

**Note:**

1. Vcc = 5V ± 5% for 12 ns devices.

**TRUTH TABLE**

Mode	$\overline{WE}$	$\overline{CE1}$	CE2	$\overline{OE}$	I/O Operation	Vcc Current
Not Selected	X	H	X	X	High-Z	Isb1, Isb2
(Power-down)	X	X	L	X	High-Z	Isb1, Isb2
Output Disabled	H	L	H	H	High-Z	Icc1, Icc2
Read	H	L	H	L	Dout	Icc1, Icc2
Write	L	L	H	X	Din	Icc1, Icc2

### ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>

Symbol	Parameter	Value	Unit
V <sub>TERM</sub>	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
T <sub>BIAS</sub>	Temperature Under Bias	-55 to +125	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C
P <sub>T</sub>	Power Dissipation	1.5	W
I <sub>OUT</sub>	DC Output Current (LOW)	20	mA

**Notes:**

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

### CAPACITANCE<sup>(1,2)</sup>

Symbol	Parameter	Conditions	Max.	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = 0V	5	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>OUT</sub> = 0V	7	pF

**Notes:**

1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T<sub>A</sub> = 25°C, f = 1 MHz, V<sub>CC</sub> = 5.0V.

### DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions		Min.	Max.	Unit
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = Min., I <sub>OH</sub> = -4.0 mA		2.4	—	V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min., I <sub>OL</sub> = 8.0 mA		—	0.4	V
V <sub>IH</sub>	Input HIGH Voltage			2.2	V <sub>CC</sub> + 0.5	V
V <sub>IL</sub>	Input LOW Voltage <sup>(1)</sup>			-0.3	0.8	V
I <sub>LI</sub>	Input Leakage	GND ≤ V <sub>IN</sub> ≤ V <sub>CC</sub>	Com. Ind.	-2 -5	2 5	μA
I <sub>LO</sub>	Output Leakage	GND ≤ V <sub>OUT</sub> ≤ V <sub>CC</sub> Outputs Disabled	Com. Ind.	-2 -5	2 5	μA

**Notes:**

1. V<sub>IL</sub> = -3.0V for pulse width less than 10 ns.

**IS61C1024 POWER SUPPLY CHARACTERISTICS<sup>(1)</sup>** (Over Operating Range)

Symbol	Parameter	Test Conditions		-12 ns		-15 ns		-20 ns		-25 ns		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
I <sub>CC1</sub>	V <sub>CC</sub> Operating Supply Current	V <sub>CC</sub> = Max., $\overline{CE} = V_{IL}$ I <sub>OUT</sub> = 0 mA, f = 0	Com.	—	140	—	140	—	140	—	140	mA
			Ind.	—	140	—	140	—	140	—	140	
I <sub>CC2</sub>	V <sub>CC</sub> Dynamic Operating Supply Current	V <sub>CC</sub> = Max., $\overline{CE} = V_{IL}$ I <sub>OUT</sub> = 0 mA, f = f <sub>MAX</sub>	Com.	—	220	—	200	—	170	—	150	mA
			Ind.	—	220	—	200	—	170	—	150	
I <sub>SB1</sub>	TTL Standby Current (TTL Inputs)	V <sub>CC</sub> = Max., V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> $\overline{CE1} \geq V_{IH}$ , f = 0 or CE2 ≤ V <sub>IL</sub> , f = 0	Com.	—	40	—	40	—	40	—	40	mA
			Ind.	—	60	—	60	—	60	—	60	
I <sub>SB2</sub>	CMOS Standby Current (CMOS Inputs)	V <sub>CC</sub> = Max., $\overline{CE1} \leq V_{CC} - 0.2V$ , CE2 ≤ 0.2V V <sub>IN</sub> > V <sub>CC</sub> - 0.2V, or V <sub>IN</sub> ≤ 0.2V, f = 0	Com.	—	30	—	30	—	30	—	30	mA
			Ind.	—	40	—	40	—	40	—	40	

**Notes:**

1. At f = f<sub>MAX</sub>, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.

**IS61C1024L POWER SUPPLY CHARACTERISTICS<sup>(1)</sup>** (Over Operating Range)

Symbol	Parameter	Test Conditions		-12 ns		-15 ns		-20 ns		-25 ns		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
I <sub>CC1</sub>	V <sub>CC</sub> Operating Supply Current	V <sub>CC</sub> = Max., $\overline{CE} = V_{IL}$ I <sub>OUT</sub> = 0 mA, f = 0	Com.	—	85	—	85	—	85	—	85	mA
			Ind.	—	110	—	110	—	110	—	110	
I <sub>CC2</sub>	V <sub>CC</sub> Dynamic Operating Supply Current	V <sub>CC</sub> = Max., $\overline{CE} = V_{IL}$ I <sub>OUT</sub> = 0 mA, f = f <sub>MAX</sub>	Com.	—	175	—	160	—	150	—	150	mA
			Ind.	—	175	—	160	—	150	—	150	
I <sub>SB1</sub>	TTL Standby Current (TTL Inputs)	V <sub>CC</sub> = Max., V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> $\overline{CE1} \geq V_{IH}$ , f = 0 or CE2 ≤ V <sub>IL</sub> , f = 0	Com.	—	40	—	40	—	40	—	40	mA
			Ind.	—	60	—	60	—	60	—	60	
I <sub>SB2</sub>	CMOS Standby Current (CMOS Inputs)	V <sub>CC</sub> = Max., $\overline{CE1} \leq V_{CC} - 0.2V$ , CE2 ≤ 0.2V V <sub>IN</sub> > V <sub>CC</sub> - 0.2V, or V <sub>IN</sub> ≤ 0.2V, f = 0	Com.	—	500	—	500	—	500	—	500	μA
			Ind.	—	750	—	750	—	750	—	750	

**Notes:**

1. At f = f<sub>MAX</sub>, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.

**READ CYCLE SWITCHING CHARACTERISTICS<sup>(1)</sup>** (Over Operating Range)

Symbol	Parameter	-12		-15 ns		-20 ns		-25 ns		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t <sub>RC</sub>	Read Cycle Time	12	—	15	—	20	—	25	—	ns
t <sub>AA</sub>	Address Access Time	—	12	—	15	—	20	—	25	ns
t <sub>OH</sub>	Output Hold Time	3	—	3	—	3	—	3	—	ns
t <sub>ACE1</sub>	$\overline{CE1}$ Access Time	—	12	—	15	—	20	—	25	ns
t <sub>ACE2</sub>	CE2 Access Time	—	12	—	15	—	20	—	25	ns
t <sub>DOE</sub>	$\overline{OE}$ Access Time	—	6	—	7	—	9	—	9	ns
t <sub>LZOE<sup>(2)</sup></sub>	$\overline{OE}$ to Low-Z Output	0	—	0	—	0	—	0	—	ns
t <sub>HZOE<sup>(2)</sup></sub>	$\overline{OE}$ to High-Z Output	0	6	0	6	0	7	0	10	ns
t <sub>LZCE1<sup>(2)</sup></sub>	$\overline{CE1}$ to Low-Z Output	2	—	2	—	3	—	3	—	ns
t <sub>LZCE2<sup>(2)</sup></sub>	CE2 to Low-Z Output	2	—	2	—	3	—	3	—	ns
t <sub>HZCE<sup>(2)</sup></sub>	$\overline{CE1}$ or CE2 to High-Z Output	0	7	0	8	0	9	0	10	ns
t <sub>PU<sup>(3)</sup></sub>	$\overline{CE1}$ or CE2 to Power-Up	0	—	0	—	0	—	0	—	ns
t <sub>PD<sup>(3)</sup></sub>	$\overline{CE1}$ or CE2 to Power-Down	—	12	—	12	—	18	—	20	ns

**Notes:**

1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1a.
2. Tested with the load in Figure 1b. Transition is measured  $\pm 500$  mV from steady-state voltage. Not 100% tested.
3. Not 100% tested.

**AC TEST CONDITIONS**

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	3 ns
Input and Output Timing and Reference Level	1.5V
Output Load	See Figures 1a and 1b

**AC TEST LOADS**

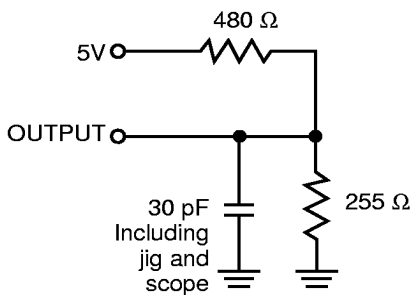


Figure 1a.

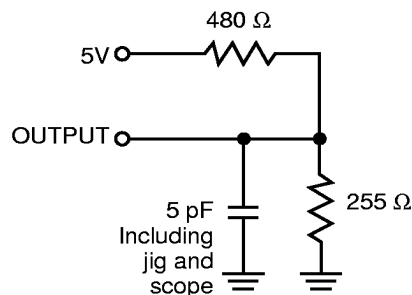
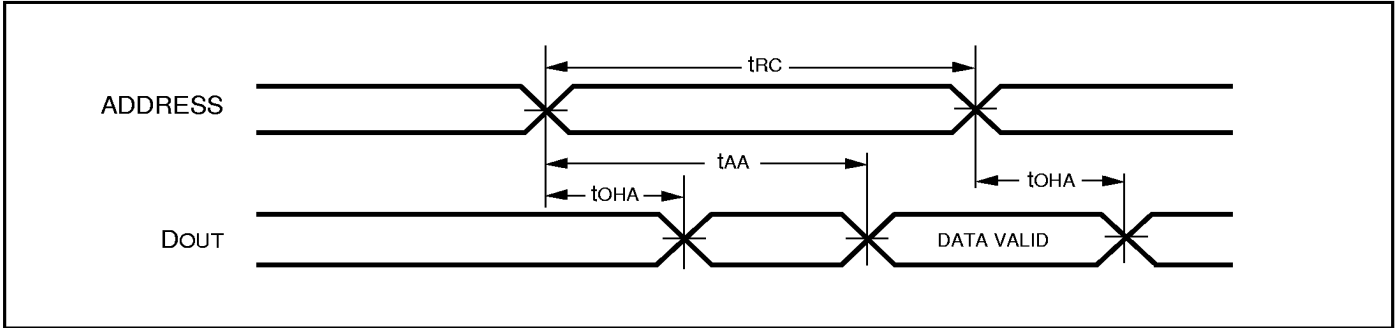


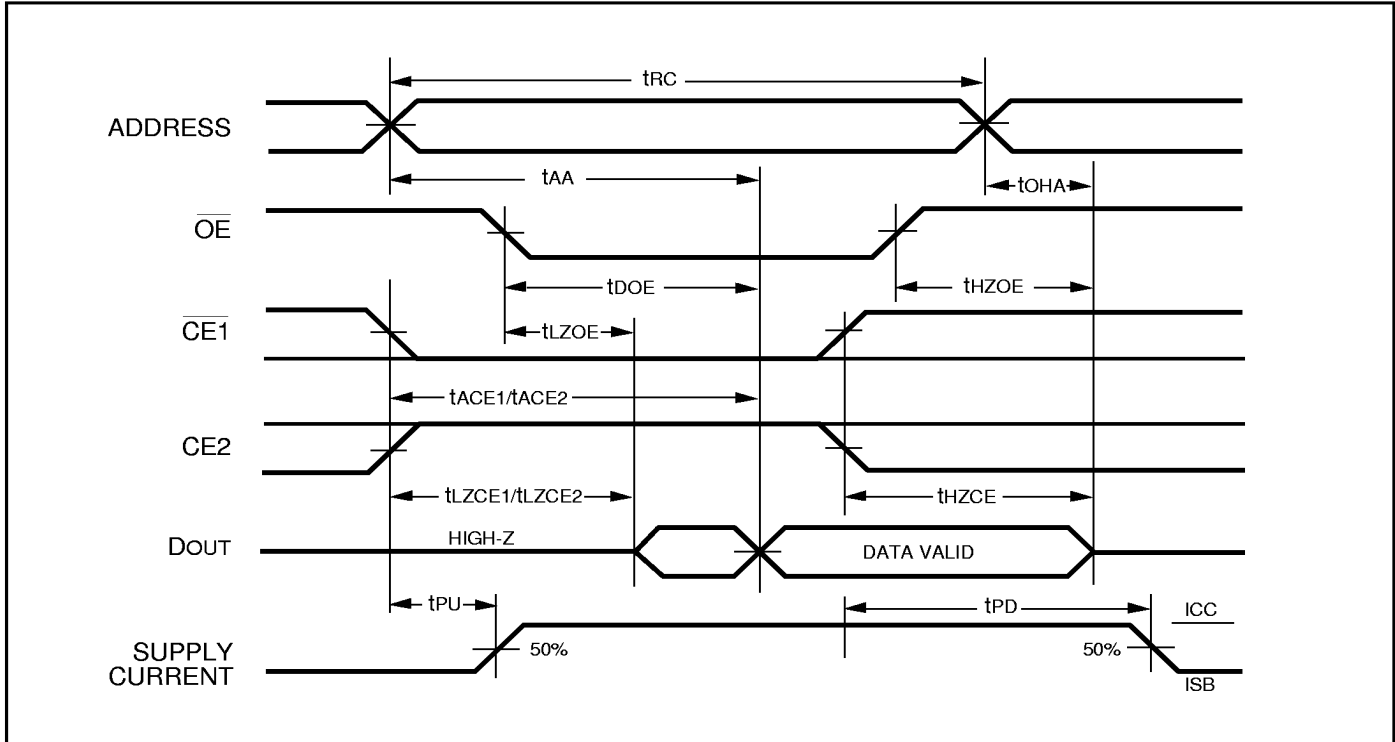
Figure 1b.

AC WAVEFORMS

READ CYCLE NO. 1<sup>(1,2)</sup>



READ CYCLE NO. 2<sup>(1,3)</sup>



Notes:

1.  $\overline{WE}$  is HIGH for a Read Cycle.
2. The device is continuously selected.  $\overline{OE}$ ,  $\overline{CE1} = V_{IL}$ ,  $CE2 = V_{IH}$ .
3. Address is valid prior to or coincident with  $\overline{CE1}$  LOW and CE2 HIGH transitions.

**WRITE CYCLE SWITCHING CHARACTERISTICS<sup>(1,3)</sup>** (Over Operating Range, Standard and Low Power)

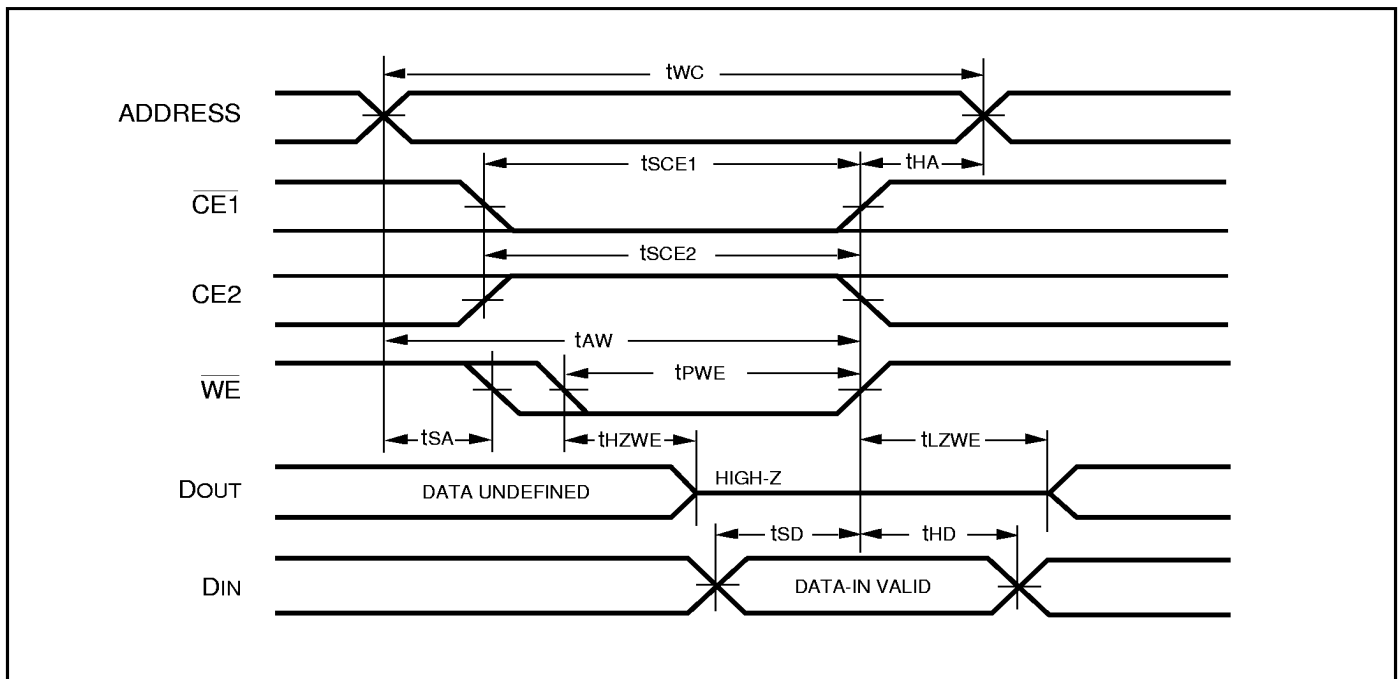
Symbol	Parameter	-12 ns		-15 ns		-20 ns		-25 ns		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t <sub>WC</sub>	Write Cycle Time	12	—	15	—	20	—	25	—	ns
t <sub>SCE1</sub>	$\overline{CE1}$ to Write End	10	—	12	—	15	—	20	—	ns
t <sub>SCE2</sub>	CE2 to Write End	10	—	12	—	15	—	20	—	ns
t <sub>AW</sub>	Address Setup Time to Write End	10	—	12	—	15	—	20	—	ns
t <sub>HA</sub>	Address Hold from Write End	0	—	0	—	0	—	0	—	ns
t <sub>SA</sub>	Address Setup Time	0	—	0	—	0	—	0	—	ns
t <sub>PWE<sup>(4)</sup></sub>	$\overline{WE}$ Pulse Width	10	—	10	—	12	—	15	—	ns
t <sub>SD</sub>	Data Setup to Write End	7	—	8	—	10	—	12	—	ns
t <sub>HD</sub>	Data Hold from Write End	0	—	0	—	0	—	0	—	ns
t <sub>HZWE<sup>(2)</sup></sub>	$\overline{WE}$ LOW to High-Z Output	—	7	—	7	—	10	—	12	ns
t <sub>LZWE<sup>(2)</sup></sub>	$\overline{WE}$ HIGH to Low-Z Output	2	—	2	—	2	—	2	—	ns

**Notes:**

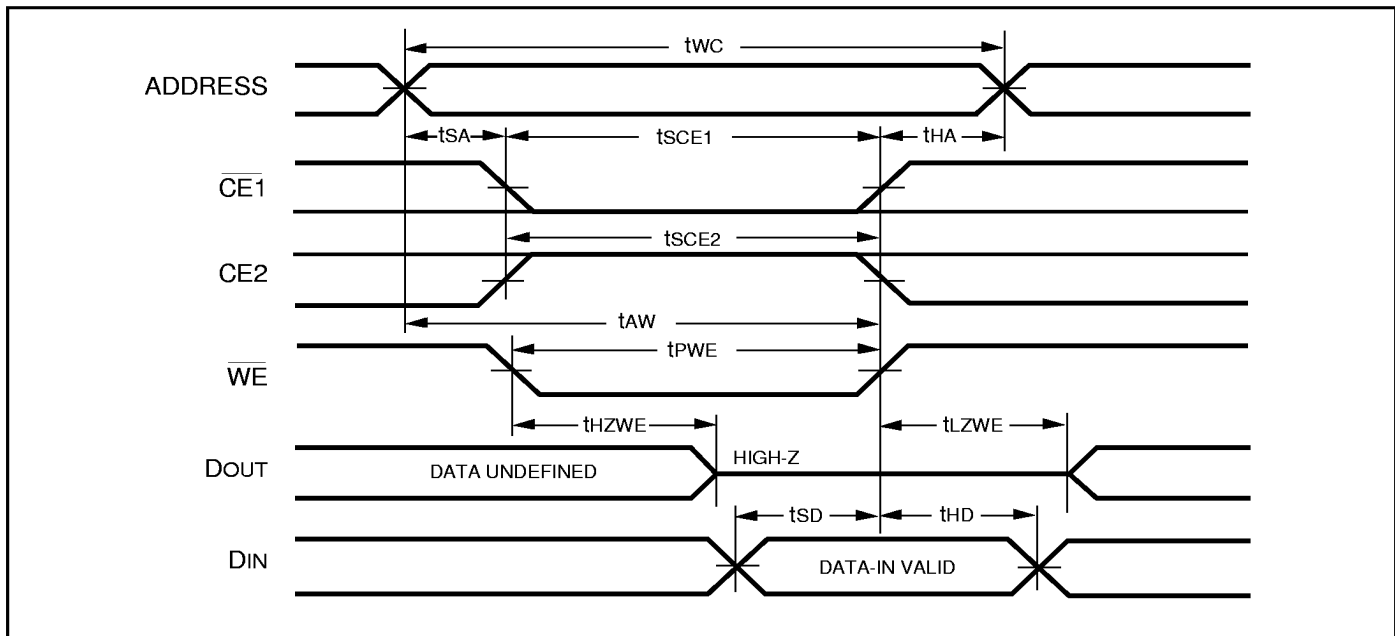
1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1a.
2. Tested with the load in Figure 1b. Transition is measured  $\pm 500$  mV from steady-state voltage. Not 100% tested.
3. The internal write time is defined by the overlap of  $\overline{CE1}$  LOW, CE2 HIGH and  $\overline{WE}$  LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the Write.
4. Tested with  $\overline{OE}$  HIGH.

**AC WAVEFORMS**

**WRITE CYCLE NO. 1 ( $\overline{WE}$  Controlled)<sup>(1,2)</sup>**



WRITE CYCLE NO. 2 ( $\overline{CE1}$ , CE2 Controlled)<sup>(1,2)</sup>



Notes:

1. The internal write time is defined by the overlap of  $\overline{CE1}$  LOW, CE2 HIGH and  $\overline{WE}$  LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the Write.
2. I/O will assume the High-Z state if  $\overline{OE} = V_{IH}$ .

**IS61C1024 STANDARD VERSION  
ORDERING INFORMATION  
Commercial Range: 0°C to +70°C**

Speed (ns)	Order Part No.	Package
12	IS61C1024-12JR	300-mil Plastic SOJ
12	IS61C1024-12NR	300-mil Plastic DIP
12	IS61C1024-12KR	400-mil Plastic SOJ
12	IS61C1024-12MR	400-mil Plastic DIP
12	IS61C1024-12TR	TSOP, Type 1
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15	IS61C1024-15J	300-mil Plastic SOJ
15	IS61C1024-15N	300-mil Plastic DIP
15	IS61C1024-15K	400-mil Plastic SOJ
15	IS61C1024-15M	400-mil Plastic DIP
15	IS61C1024-15T	TSOP, Type 1
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20	IS61C1024-20J	300-mil Plastic SOJ
20	IS61C1024-20N	300-mil Plastic DIP
20	IS61C1024-20K	400-mil Plastic SOJ
20	IS61C1024-20M	400-mil Plastic DIP
20	IS61C1024-20T	TSOP, Type 1
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25	IS61C1024-25J	300-mil Plastic SOJ
25	IS61C1024-25N	300-mil Plastic DIP
25	IS61C1024-25K	400-mil Plastic SOJ
25	IS61C1024-25M	400-mil Plastic DIP
25	IS61C1024-25T	TSOP, Type 1

**IS61C1024 STANDARD VERSION  
ORDERING INFORMATION  
Industrial Range: -40°C to +85°C**

Speed (ns)	Order Part No.	Package
12	IS61C1024-12JRI	300-mil Plastic SOJ
12	IS61C1024-12NRI	300-mil Plastic DIP
12	IS61C1024-12KRI	400-mil Plastic SOJ
12	IS61C1024-12MRI	400-mil Plastic DIP
12	IS61C1024-12TRI	TSOP, Type 1
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15	IS61C1024-15JI	300-mil Plastic SOJ
15	IS61C1024-15NI	300-mil Plastic DIP
15	IS61C1024-15KI	400-mil Plastic SOJ
15	IS61C1024-15MI	400-mil Plastic DIP
15	IS61C1024-15TI	TSOP, Type 1
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20	IS61C1024-20JI	300-mil Plastic SOJ
20	IS61C1024-20NI	300-mil Plastic DIP
20	IS61C1024-20KI	400-mil Plastic SOJ
20	IS61C1024-20MI	400-mil Plastic DIP
20	IS61C1024-20TI	TSOP, Type 1
<hr/>		
25	IS61C1024-25JI	300-mil Plastic SOJ
25	IS61C1024-25NI	300-mil Plastic DIP
25	IS61C1024-25KI	400-mil Plastic SOJ
25	IS61C1024-25MI	400-mil Plastic DIP
25	IS61C1024-25TI	TSOP, Type 1



**IS61C1024L LOW POWER VERSION  
ORDERING INFORMATION  
Commercial Range: 0°C to +70°C**

Speed (ns)	Order Part No.	Package
12	IS61C1024L-12JR	300-mil Plastic SOJ
	IS61C1024L-12NR	300-mil Plastic DIP
	IS61C1024L-12KR	400-mil Plastic SOJ
	IS61C1024L-12MR	400-mil Plastic DIP
	IS61C1024L-12TR	TSOP, Type 1
15	IS61C1024L-15J	300-mil Plastic SOJ
	IS61C1024L-15N	300-mil Plastic DIP
	IS61C1024L-15K	400-mil Plastic SOJ
	IS61C1024L-15M	400-mil Plastic DIP
	IS61C1024L-15T	TSOP, Type 1
20	IS61C1024L-20J	300-mil Plastic SOJ
	IS61C1024L-20N	300-mil Plastic DIP
	IS61C1024L-20K	400-mil Plastic SOJ
	IS61C1024L-20M	400-mil Plastic DIP
	IS61C1024L-20T	TSOP, Type 1
25	IS61C1024L-25J	300-mil Plastic SOJ
	IS61C1024L-25N	300-mil Plastic DIP
	IS61C1024L-25K	400-mil Plastic SOJ
	IS61C1024L-25M	400-mil Plastic DIP
	IS61C1024L-25T	TSOP, Type 1

**IS61C1024L LOW POWER VERSION  
ORDERING INFORMATION  
Industrial Range: -40°C to +85°C**

Speed (ns)	Order Part No.	Package
12	IS61C1024L-12JRI	300-mil Plastic SOJ
	IS61C1024L-12NRI	300-mil Plastic DIP
	IS61C1024L-12KRI	400-mil Plastic SOJ
	IS61C1024L-12TRI	TSOP, Type 1
15	IS61C1024L-15JI	300-mil Plastic SOJ
	IS61C1024L-15NI	300-mil Plastic DIP
	IS61C1024L-15KI	400-mil Plastic SOJ
	IS61C1024L-15TI	TSOP, Type 1
20	IS61C1024L-20JI	300-mil Plastic SOJ
	IS61C1024L-20NI	300-mil Plastic DIP
	IS61C1024L-20KI	400-mil Plastic SOJ
	IS61C1024L-20TI	TSOP, Type 1
25	IS61C1024L-25JI	300-mil Plastic SOJ
	IS61C1024L-25NI	300-mil Plastic DIP
	IS61C1024L-25KI	400-mil Plastic SOJ
	IS61C1024L-25TI	TSOP, Type 1